onsemi

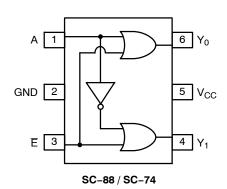
1-to-2 Decoder/ Demultiplexer

NL7SZ19

The NL7SZ19 is a 1-to-2 decoder. When the output enable (\overline{E}) is Low, the device passes data at input A to outputs Y0 (true) and Y1 (complement). The NL7SZ19 can also be used as a 1-to-2 demultiplexer. As a demultiplexer, data at input E is routed to either Y0 or Y1 depending on the state of A. The device operates over the voltage range from 1.65 V to 5.5 V.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 2.7 ns t_{PD} at $V_{CC} = 5 V$ (Typ)
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Sink 32 mA at 5.0 V
- Available in SC-88, SC-74 and UDFN6 Packages
- Chip Complexity < 100 FETs
- -Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



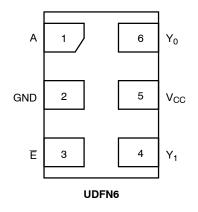


Figure 1. Pinout (Top View)





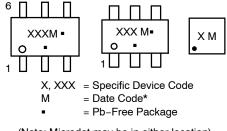
SC-88 DF SUFFIX CASE 419B

SC-74 CASE 318F-05



UDFN6, 1.2x1.0, 0.4P CASE 517AA-01





(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

PIN ASSIGNMENT

Pin	Function
1	А
2	GND
3	Ē
4	Y ₁
5	V _{CC}
6	Y ₀

FUNCTION TABLE

E	Α	$Y_0 = A + \overline{E}$	$Y_1 = \overline{A} + \overline{E}$
L	L	L	Н
L	Н	Н	L
Н	Н	Н	Н
Н	L	Н	Н

MAXIMUM RATINGS

Symbol	Characteristics		Value	Unit	
V _{CC}	DC Supply Voltage		-0.5 to +6.5	V	
V _{IN}	DC Input Voltage		–0.5 to +6.5	V	
V _{OUT}		Mode (High or Low State) Tri-State Mode (Note 1) -Down Mode (V _{CC} = 0 V)	$\begin{array}{c} -0.5 \text{ to } V_{CC} + 0.5 \\ -0.5 \text{ to } +6.5 \\ -0.5 \text{ to } +6.5 \end{array}$	V	
I _{IK}	DC Input Diode Current	V _{IN} < GND	-50	mA	
I _{OK}	DC Output Diode Current	V _{OUT} < GND	-50	mA	
I _{OUT}	DC Output Source/Sink Current		±50	mA	
I_{CC} or I_{GND}	DC Supply Current per Supply Pin or Ground Pin		±100	mA	
T _{STG}	Storage Temperature Range		-65 to +150	°C	
ΤL	Lead Temperature, 1 mm from Case for 10 secs		260	°C	
ТJ	Junction Temperature Under Bias		+150	°C	
θ_{JA}	Thermal Resistance (Note 2)	SC-88 SC-74 UDFN6	377 320 154	°C/W	
P _D	Power Dissipation in Still Air	SC-88 SC-74 UDFN6	332 390 812	mW	
MSL	Moisture Sensitivity		Level 1	-	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-	
V_{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V	
I _{Latchup}	Latchup Performance (Note 4)		±100	mA	

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RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	1.65	5.5	V
V _{IN}	DC Input Voltage	0	5.5	V
V _{OUT}	DC Output Voltage Active–Mode (High or Low State) Tri–State Mode (Note 1) Power–Down Mode (V _{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	
T _A	Operating Temperature Range	-55	+125	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 1.65 V \text{ to } 1.95 V \\ V_{CC} = 2.3 V \text{ to } 2.7 V \\ V_{CC} = 3.0 V \text{ to } 3.6 V \\ V_{CC} = 4.5 V \text{ to } 5.5 V$	0 0 0 0	20 20 10 5	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			v _{cc}	Т	A = 25°	С	–55°C ≤ T _A ≤ 125°C		
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Units
V _{IH}	High-Level Input	-	1.65 to 1.95	$0.65 \times V_{CC}$	-	-	$0.65 \times V_{CC}$	-	V
	Voltage		2.3 to 5.5	$0.70 \times V_{CC}$	-	-	$0.70 \times V_{CC}$	-	
V _{IL}	Low-Level Input	-	1.65 to 1.95	-	-	$0.35 \times V_{CC}$	-	$0.35 \times V_{CC}$	V
	Voltage		2.3 to 5.5	-	-	$0.30 \times V_{CC}$	-	$0.30 \times V_{CC}$	
V _{OH}	High-Level Output Voltage	$ \begin{array}{l} V_{IN} = V_{IH} \text{ or } V_{IL} \\ I_{OH} = -100 \ \mu A \\ I_{OH} = -4 \ m A \\ I_{OH} = -8 \ m A \\ I_{OH} = -16 \ m A \\ I_{OH} = -24 \ m A \\ I_{OH} = -32 \ m A \end{array} $	1.65 to 5.5 1.65 2.3 3 3 4.5	V _{CC} - 0.1 1.29 1.9 2.4 2.3 3.8	V _{CC} 1.52 2.1 2.7 2.5 4		V _{CC} - 0.1 1.29 1.9 2.4 2.3 3.8		V
V _{OL}	Low-Level Output Voltage		1.65 to 5.5 1.65 2.3 3 3 4.5		- 0.08 0.12 0.24 0.26 0.31	0.1 0.24 0.3 0.4 0.55 0.55		0.1 0.24 0.3 0.4 0.55 0.55	V
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	1.65 to 5.5	-	-	±0.1	-	±1.0	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	-	-	1.0	-	10	μΑ
Icc	Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5	-	-	1.0	-	10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

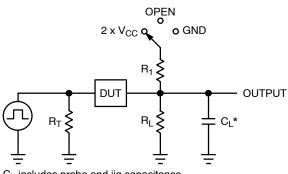
AC ELECTRICAL CHARACTERISTICS

			V _{cc}	T _A = 25°C		С	–55°C ≤ T _/		
Symbol	Parameter	Condition	(Ň)	Min	Тур	Max	Min	Max	Units
t _{PLH,}	t _{PLH,} Propagation Delay, A to Y t _{PHL} (Figures 2 and 3)	R_L = 1 MΩ, C_L = 15 pF	1.65 to 1.95	-	6.2	10.5	-	11.0	ns
PHL		R_L = 1 M Ω , C_L = 15 pF	2.3 to 2.7	-	3.6	6.0	-	6.4	
		R_L = 1 M Ω , C_L = 15 pF	3.0 to 3.6	-	2.9	4.1	-	4.5	
		R_L = 500 Ω , C_L = 50 pF		-	3.2	5.1	-	5.4	
		R_L = 1 M Ω , C_L = 15 pF	4.5 to 5.5	-	2.4	3.2	-	3.5	
		R_L = 500 Ω , C_L = 50 pF		_	2.7	4.0	-	4.3	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	2.5	pF
C _{OUT}	Output Capacitance	V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	2.5	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V _{CC} = 3.3 V, V _{IN} = 0 V or V _{CC} 10 MHz, V _{CC} = 5.5 V, V _{IN} = 0 V or V _{CC}	9 11	pF

5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

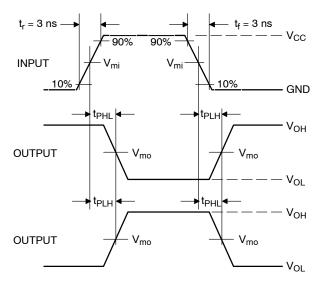


Switch Position	C _L , pF	R_{L}, Ω	R ₁ , Ω		
Open	See AC Characteristics Table				
$2 \times V_{CC}$	50	500	500		
GND	50	500	500		
	Position Open 2 x V _{CC}	Position See AC Character 0pen See AC Character 2 x V _{CC} 50	Position See AC Characteristics Tall 0pen See AC Characteristics Tall 2 x V _{CC} 50		

X = Don't Care

 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$ f = 1 MHz

Figure 2. Test Circuit



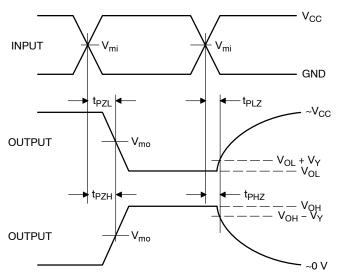


Figure 3. Switching Waveforms

		Vm		
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t _{PZL} , t _{PLZ} , t _{PZH} , t _{PHZ}	V _Y , V
1.65 to 1.95	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.15
2.3 to 2.7	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.15
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3

NL7SZ19

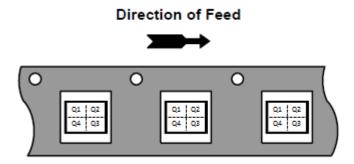
DEVICE ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
NL7SZ19DFT2G	SC-88	LE	Q4	3000 / Tape & Reel
NL7SZ19DFT2G-Q*	SC-88	LE	Q4	3000 / Tape & Reel
NL7SZ19DBVT1G	SC-74	AK	Q4	3000 / Tape & Reel
NL7SZ19MU2TBG	UDFN6, 1.2 x 1.0, 0.4P	U	Q2	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging

Specifications Brochure, BRD8011/D. *-Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

PIN 1 ORIENTATION IN TAPE AND REEL



NL7SZ19

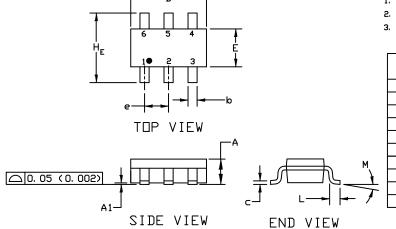
PACKAGE DIMENSIONS

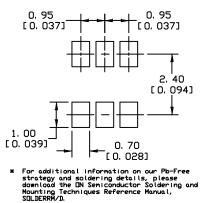
SC-74 CASE 318F ISSUE P



- 1. DIMENSIONING AND TOLERANCING PER ASME Y14. 5M, 1994
- 2. CONTROLLING DIMENSION: INCHES
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.

	MI	LLIMETER	25	INCHES					
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.			
Α	0. 90	1.00	1.10	0. 035	0. 039	0. 043			
A1	0. 01	0.06	0.10	0. 001	0. 002	0. 004			
ю	0. 25	0. 37	0. 50	0. 010	0.015	0. 020			
с	0.10	0.18	0. 26	0. 004	0. 007	0. 010			
D	2, 90	3. 00	3.10	0.114	0.118	0. 122			
E	1.30	1. 50	1. 70	0. 051	0. 059	0. 067			
e	0.85	0. 95	1. 05	0. 034	0. 037	0. 041			
Η _E	2. 50	2. 75	3. 00	0. 099	0. 108	0.118			
L	0. 20	0.40	0. 60	0. 008	0. 016	0. 024			
м	0*		10*	0*		10*			



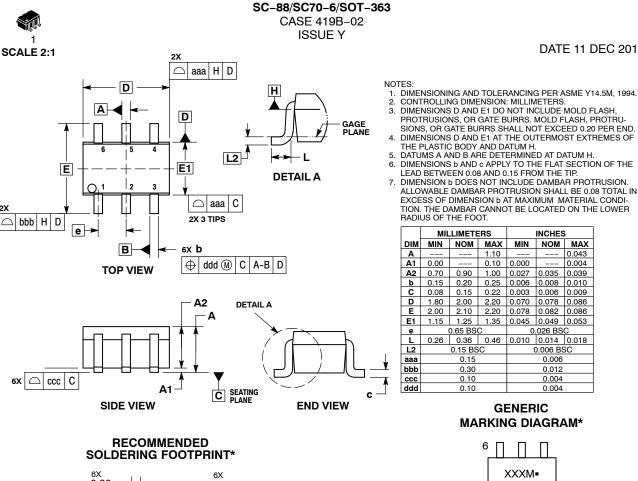


SOLDERING FOOTPRINT

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DOSEM

DATE 11 DEC 2012



6X 0.30 -0.66 2 50 0.65 PITCH DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

- CONTROLLING DIMENSION: MILLIMETERS. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRU-SIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H. DATUMS A AND B ARE DETERMINED AT DATUM H. DIMENSIONS b AND ¢ APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. DIMENSION b DOCE NOT INCLUDE DAMAGE PROTEINSION

- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDI-TION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS				INCHES	3	
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α			1.10			0.043	
A1	0.00		0.10	0.000		0.004	
A2	0.70	0.90	1.00	0.027	0.035	0.039	
b	0.15	0.20	0.25	0.006	0.008	0.010	
С	0.08	0.15	0.22	0.003	0.006	0.009	
D	1.80	2.00	2.20	0.070	0.078	0.086	
Е	2.00	2.10	2.20	0.078	0.082	0.086	
E1	1.15	1.25	1.35	0.045	0.049	0.053	
е	(0.65 BS	С	0.026 BSC			
L	0.26	0.36	0.46	0.010	0.014	0.018	
L2	0.15 BSC			0.006 BSC			
aaa	0.15			0.006			
bbb	0.30			0.012			
ccc	0.10			0.004			
ddd		0.10			0.004		

GENERIC **MARKING DIAGRAM***



XXX = Specific Device Code

- = Date Code* Μ
- = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE Y

DATE 11 DEC 2012

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13:	STYLE 14:	STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:
PIN 1. ANODE	PIN 1. VREF	PIN 1. ANODE 1	PIN 1. BASE 1	PIN 1. BASE 1	PIN 1. VIN1
2. N/C	2. GND	2. ANODE 2	2. EMITTER 2	2. EMITTER 1	2. VCC
3. COLLECTOR	3. GND	3. ANODE 3	3. COLLECTOR 2	3. COLLECTOR 2	3. VOUT2
4. EMITTER	4. IOUT	4. CATHODE 3	4. BASE 2	4. BASE 2	4. VIN2
5. BASE	5. VEN	5. CATHODE 2	5. EMITTER 1	5. EMITTER 2	5. GND
6. CATHODE	6. VCC	6. CATHODE 1	6. COLLECTOR 1	6. COLLECTOR 1	6. VOUT1
STYLE 19:	STYLE 20:	STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:
PIN 1. I OUT	PIN 1. COLLECTOR	PIN 1. ANODE 1	PIN 1. D1 (i)	PIN 1. Vn	PIN 1. CATHODE
2. GND	2. COLLECTOR	2. N/C	2. GND	2. CH1	2. ANODE
3. GND	3. BASE	3. ANODE 2	3. D2 (i)	3. Vp	3. CATHODE
4. V CC	4. EMITTER	4. CATHODE 2	4. D2 (c)	4. N/C	4. CATHODE
5. V EN	5. COLLECTOR	5. N/C	5. VBUS	5. CH2	5. CATHODE
6. V REF	6. COLLECTOR	6. CATHODE 1	6. D1 (c)	6. N/C	6. CATHODE
STYLE 25:	STYLE 26:	STYLE 27:	STYLE 28:	STYLE 29:	STYLE 30:
PIN 1. BASE 1	PIN 1. SOURCE 1	PIN 1. BASE 2	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. SOURCE 1
2. CATHODE	2. GATE 1	2. BASE 1	2. DRAIN	2. ANODE	2. DRAIN 2
3. COLLECTOR 2	3. DRAIN 2	3. COLLECTOR 1	3. GATE	3. COLLECTOR	3. DRAIN 2
4. BASE 2	4. SOURCE 2	4. EMITTER 1	4. SOURCE	4. EMITTER	4. SOURCE 2
5. EMITTER	5. GATE 2	5. EMITTER 2	5. DRAIN	5. BASE/ANODE	5. GATE 1
6. COLLECTOR 1	6. DRAIN 1	6. COLLECTOR 2	6. DRAIN	6. CATHODE	6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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